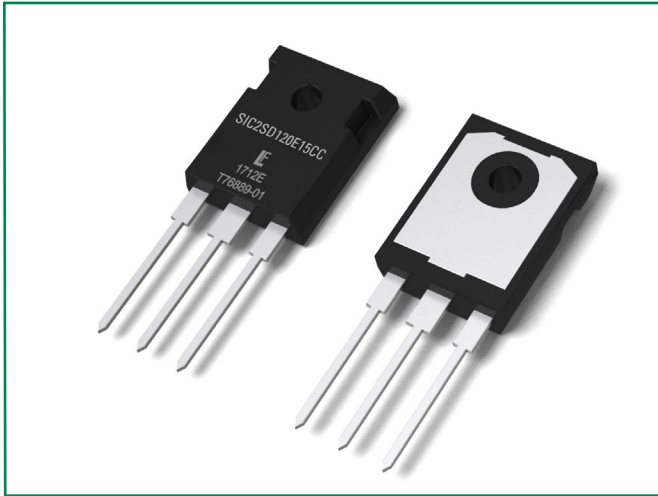


LSIC2SD120E15CC

HF RoHS Pb



Description

This series of silicon carbide (SiC) Schottky diodes has negligible reverse recovery current, high surge capability, and a maximum operating junction temperature of 175 °C. This diode series is ideal for applications where improvements in efficiency, reliability, and thermal management are desired.

Features

- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes

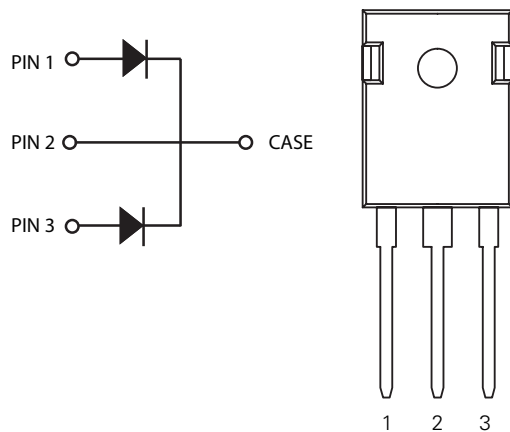
Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Uninterruptible power supplies
- Solar inverters
- Industrial motor drives
- EV charging stations

Environmental

- Littelfuse "RoHS" logo = RoHS conform
- Littelfuse "HF" logo = **HF** Halogen Free
- Littelfuse "Pb-free" logo = Pb-free lead plating

Circuit Diagram TO-247-3L



Maximum Ratings

Characteristics	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	-	1200	V
DC Blocking Voltage	V_R	$T_J = 25\text{ °C}$	1200	V
Continuous Forward Current (Per Leg/Component)	I_F	$T_C = 25\text{ °C}$	24.5/49	A
		$T_C = 135\text{ °C}$	12/24	
		$T_C = 154\text{ °C}$	8/16	
Non-Repetitive Forward Surge Current (Per Leg)	I_{FSM}	$T_C = 25\text{ °C}, T_P = 10\text{ ms}$, Half sine pulse	65	A
Power Dissipation (Per Leg/Component)	P_{Tot}	$T_C = 25\text{ °C}$	125/250	W
		$T_C = 110\text{ °C}$	54/108	
Operating Junction Temperature	T_J	-	-55 to 175	°C
Storage Temperature	T_{STG}	-	-55 to 150	°C
Soldering Temperature	T_{sold}	-	260	°C

Electrical Characteristics (Per Leg)

Characteristics	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F = 8 \text{ A}, T_J = 25^\circ\text{C}$	-	1.5	1.8	V
		$I_F = 8 \text{ A}, T_J = 175^\circ\text{C}$	-	2.2	-	
Reverse Current	I_R	$V_R = 1200 \text{ V}, T_J = 25^\circ\text{C}$	-	<1	100	μA
		$V_R = 1200 \text{ V}, T_J = 175^\circ\text{C}$	-	10	-	
Total Capacitance	C	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$	-	454	-	pF
		$V_R = 400 \text{ V}, f = 1 \text{ MHz}$	-	45	-	
		$V_R = 800 \text{ V}, f = 1 \text{ MHz}$	-	33	-	
Total Capacitive Charge	Q_C	$V_R = 800 \text{ V}, Q_C = \int_0^{V_R} C(V) dV$	-	47	-	nC

Footnote: $T_J = +25^\circ\text{C}$ unless otherwise specified

Thermal Characteristics

Characteristics	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Thermal Resistance (Per Leg/Component)	$R_{\theta JC}$	-	-	0.6 / 1.2	-	$^\circ\text{C/W}$

Figure 1: Typical Forward Characteristics (Per Leg)

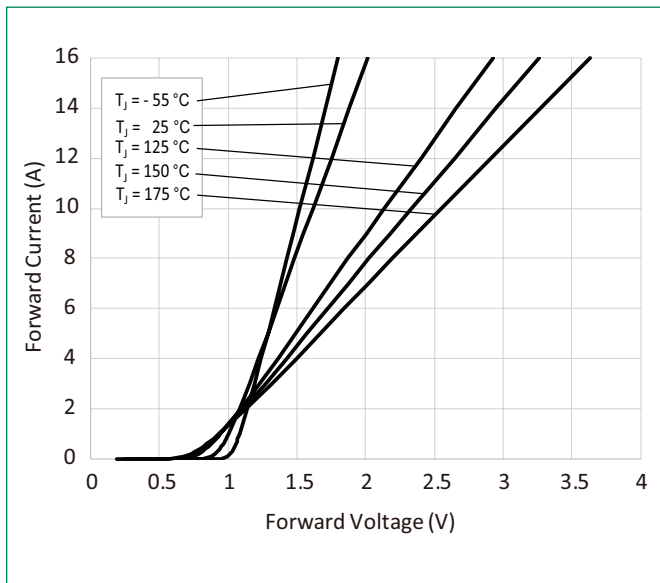


Figure 2: Typical Reverse Characteristics (Per Leg)

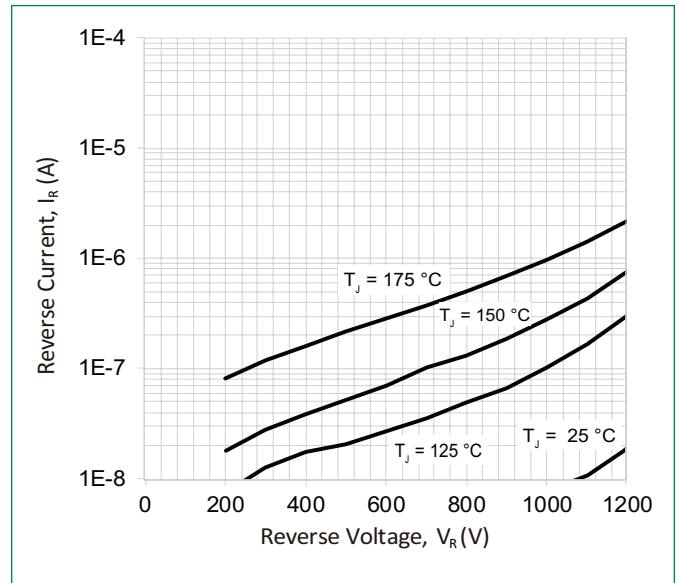


Figure 3: Power Derating (Per Leg)

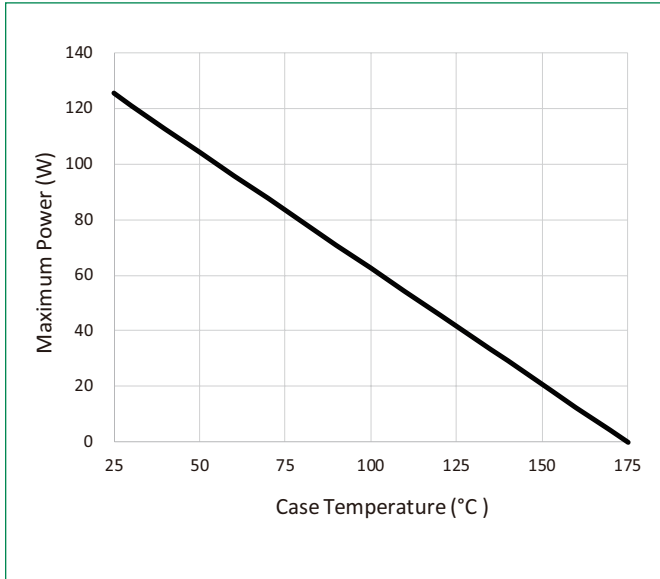


Figure 4: Current Derating (Per Leg)

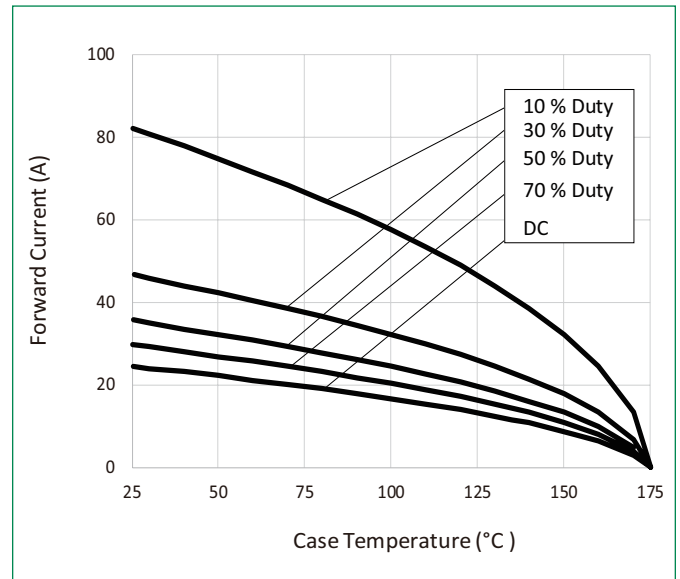


Figure 5: Capacitance vs. Reverse Voltage (Per Leg)

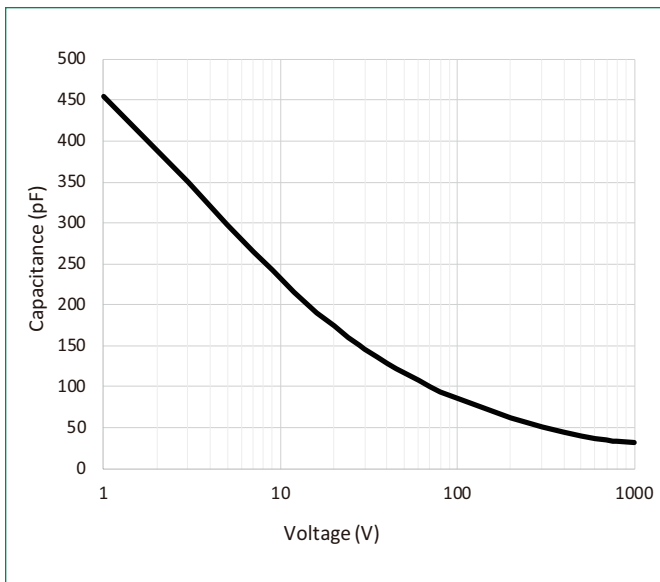


Figure 6: Capacitive Charge vs. Reverse Voltage (Per Leg)

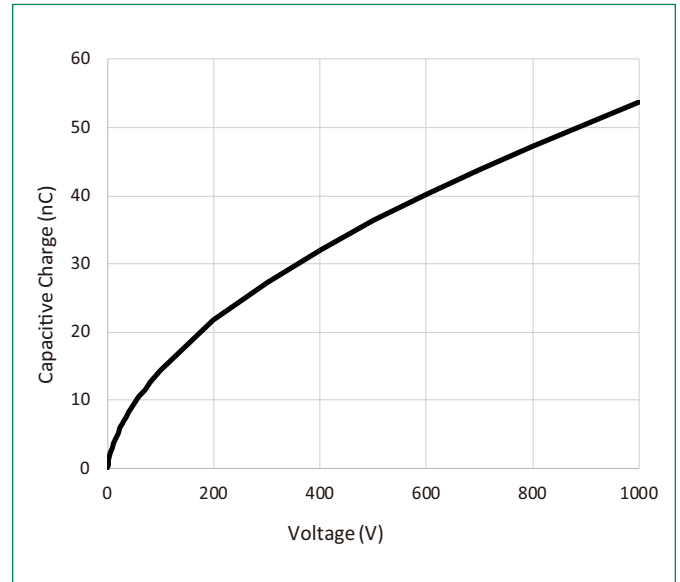


Figure 7: Stored Energy vs. Reverse Voltage (Per Leg)

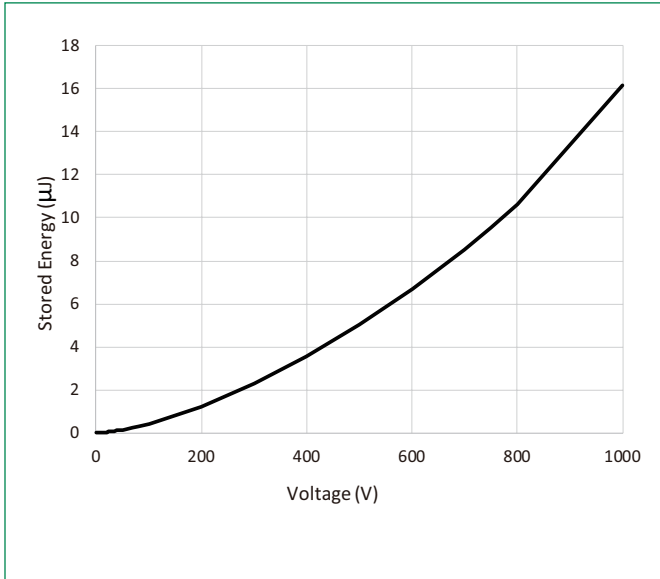
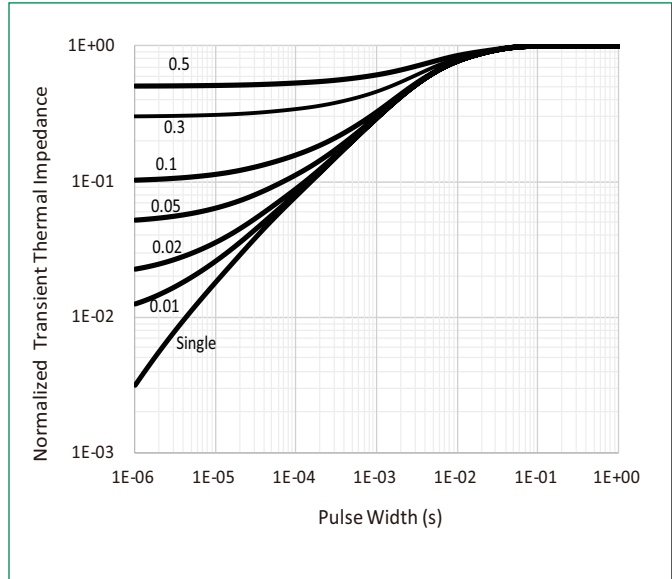
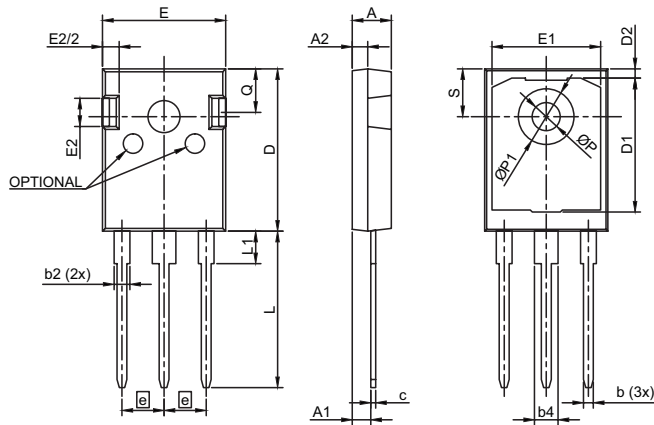


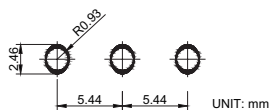
Figure 8: Transient Thermal Impedance (Per Component)



Package Dimensions TO-247-3L



Recommended Hole Pattern Layout



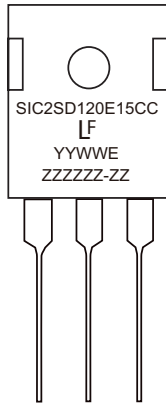
- Notes:
1. Dimensions are in millimeters
 2. Dimension D, E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These measured at the outermost extreme of plastic body.
 3. ØP to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 0.154"

Symbol	Millimeters		
	Min	Nom	Max
A	4.80	5.03	5.20
A1	2.25	2.38	2.54
A2	1.85	1.98	2.11
b	0.99	-	1.40
b2	1.65	-	2.39
b4	2.59	-	3.43
c	0.38	0.64	0.89
D	20.80	20.96	21.34
D1	13.50	-	-
D2	0.51	1.19	1.35
e	5.44 BSC		
E	15.75	15.90	16.13
E1	13.06	14.02	14.15
E2	4.19	4.32	4.83
L	19.81	20.19	20.57
L1	3.81	4.19	4.45
ØP	3.55	3.61	3.66
ØP1	7.06	7.19	7.32
Q	5.49	5.61	6.20
S	6.05	6.17	6.30

GEN2 SiC Schottky Diode

LSIC2SD120E15CC, 1200 V, 15 A, TO-247-3L

Part Numbering and Marking System

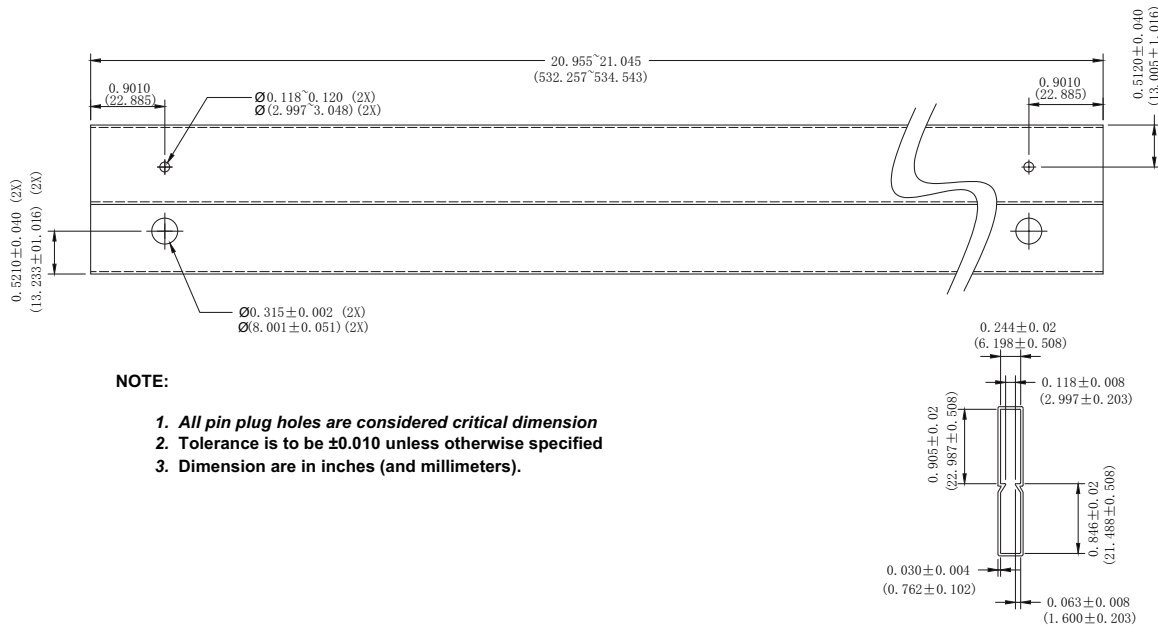


SIC = SiC
 2 = Gen2
 SD = Schottky Diode
 120 = Voltage Rating (1200 V)
 E = TO-247-3L
 15 = Current Rating (15 A)
 CC = Common Cathode
 YY = Year
 WW = Week
 E = Special Code
 ZZZZZZ-ZZ = Lot Number

Packing Options

Part Number	Marking	Packing Mode	M.O.Q
LSIC2SD120E15CC	SIC2SD120E15CC	Tube (30pcs)	450

Packing Specification TO-247-3L



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